



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

HIRASE, Masaki et al.

Serial No.: 09/908,941

Filed: July 20, 2001

Group Art Unit: 2812

Examiner: Jennifer M. Kennedy

P.T.O. Confirmation No.: 1043

For. SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE
SAME

AMENDMENT AFTER FINAL REJECTION

Commissioner for Patents
Washington, D.C. 20231

Date: February 14, 2003

Sir:

In response to the Office Action dated November 18, 2002, please amend the
above-identified application as set forth below:

IN THE CLAIMS:

Please amend claims 3 and 7 as follows:

3. (Twice Amended) A method for manufacturing a semiconductor device, the
method comprising:

forming an element partitioning trench and a mask aligning trench in a
semiconductor substrate;

depositing an insulation in the element partitioning trench and the mask
aligning trench, wherein the step of depositing includes performing a chemical vapor

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